60V Dual N Channel MOSFETs

PDEV68A8Z

General Description

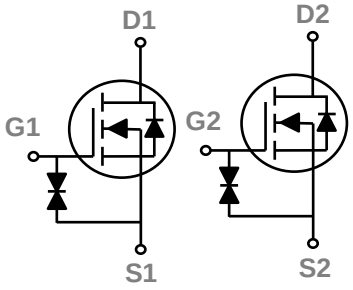
These dual N Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
60V	3Ω	300mA

Features

- *60V,300mA, RDS(ON) =3Ω@VGS = 10V*
- *Improved dv/dt capability*
- *Green Device Available*
- *G-S ESD Protection Diode Embedded*
- *ESD protected up to 2KV*

SOT363 Dual Pin Configuration



Applications

- *Notebook*
- *Load Switch*
- *Networking*
- *Hand-held Instruments*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current – Continuous (T_A=25℃)	300	mA
	Drain Current – Continuous (T_A=70℃)	240	mA
I_{DM}	Drain Current – Pulsed[1]	1.2	A
P_D	Power Dissipation (T_C=25℃)	278	mW
	Power Dissipation – Derate above 25℃	2.2	mW/℃
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	450	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.05	---	V/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=48V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=48V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±20	uA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=0.3A	---	1.3	3	Ω
		V_{GS}=4.5V , I_D=0.2A	---	1.5	4	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	2	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-3	---	mV/℃

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=30V , V_{GS}=10V , I_D=0.3A	---	2	5	nC
Q_{gs}	Gate-Source Charge[2,3]		---	0.9	3	
Q_{gd}	Gate-Drain Charge[2,3]		---	0.4	2	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=30V , V_{GS}=10V , R_G=6Ω I_D=0.3A	---	3	6	ns
T_r	Rise Time[2,3]		---	5	10	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	14	27	
T_f	Fall Time[2,3]		---	9	17	pF
C_{iss}	Input Capacitance	V_{DS}=48V , V_{GS}=0V , F=1MHz		65	130	
C_{oss}	Output Capacitance		---	21	40	
C_{rss}	Reverse Transfer Capacitance		---	8.5	15	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	300	mA
I_{SM}	Pulsed Source Current		---	---	600	mA
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=0.2A , T_J=25℃	---	---	1	V
T_{rr}	Reverse Recovery Time	V_R=50V,IS=0.3A	---	4.5	---	ns
Q_{rr}	Reverse Recovery Charge	di/dt=100A/μs TJ=25℃	---	2	---	nC

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

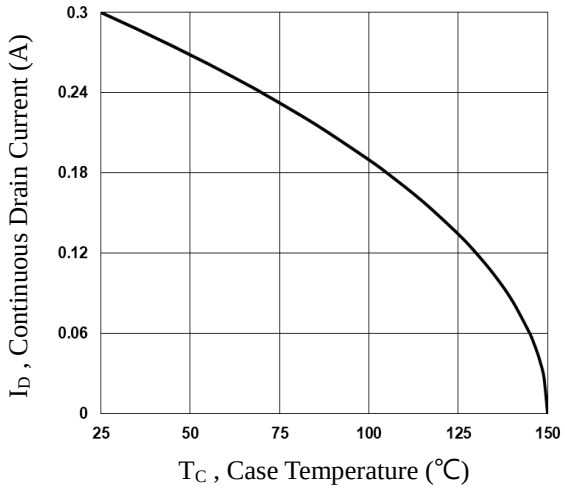


Fig.1 Continuous Drain Current vs. T_C

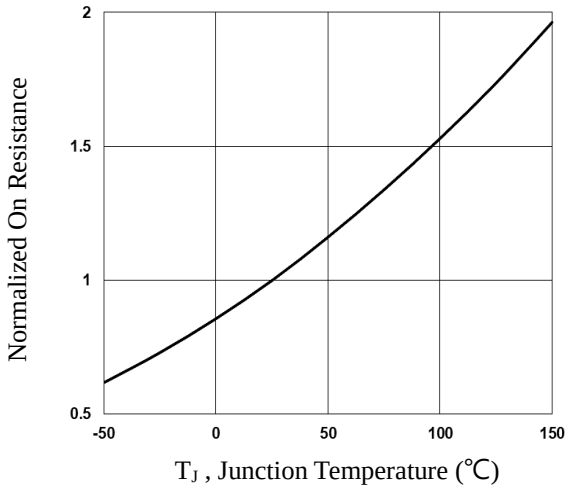


Fig.2 Normalized RDSON vs. T_J

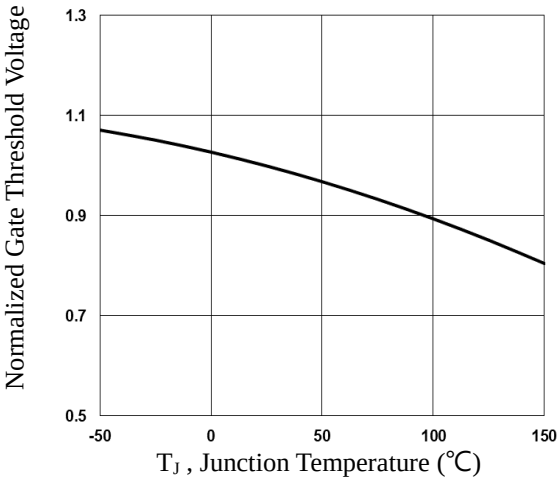


Fig.3 Normalized V_{th} vs. T_J

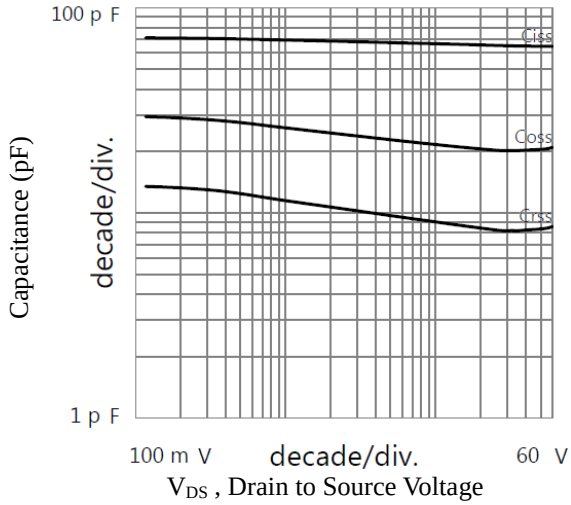


Fig.4 Capacitance Characteristics

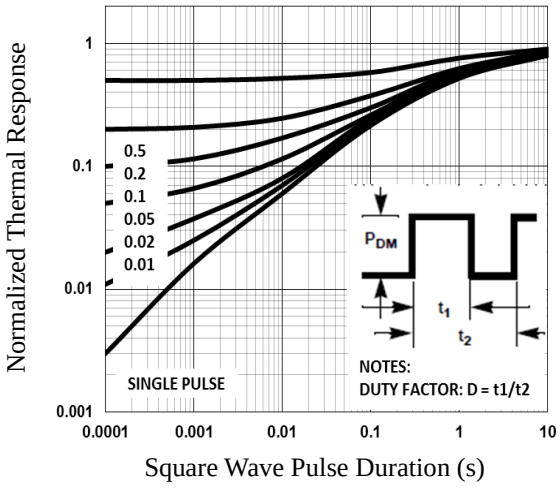


Fig.5 Normalized Transient Impedance

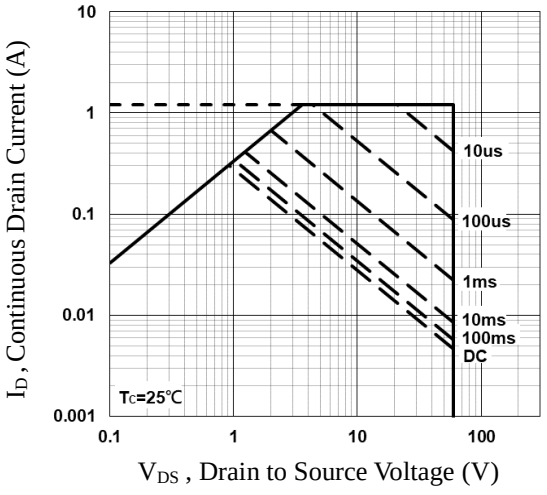
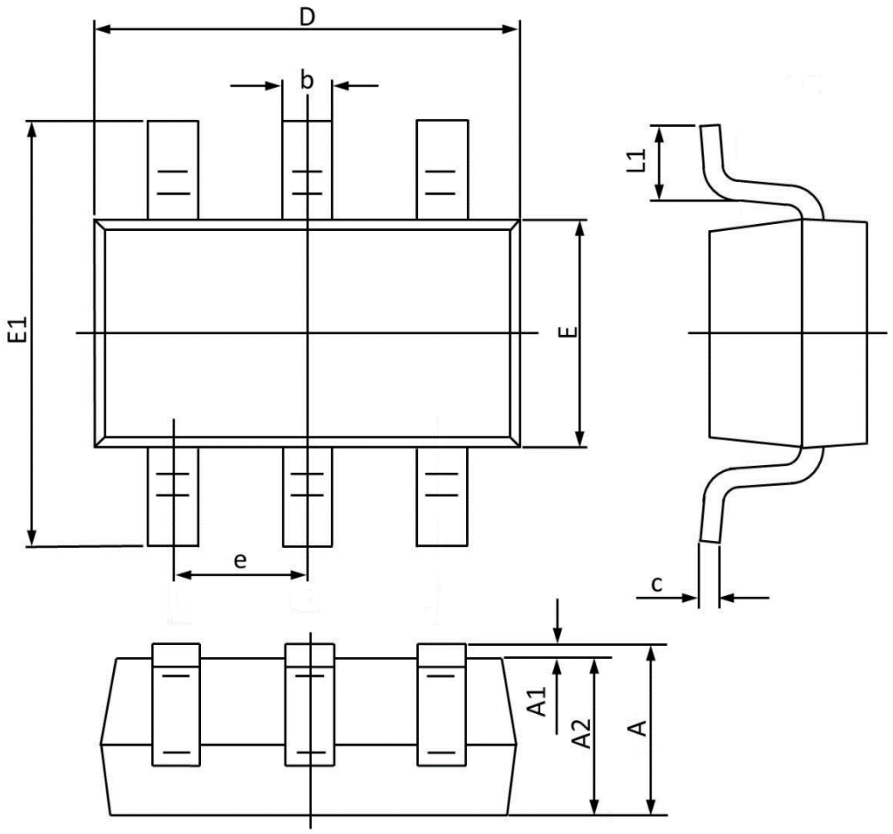


Fig.6 Maximum Safe Operation Area

SOT363 Dual PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
A1	0.100	0.000	0.004	0.000
A2	1.000	0.800	0.039	0.031
b	0.330	0.100	0.013	0.004
c	0.250	0.100	0.010	0.004
D	2.200	1.800	0.087	0.071
E	1.350	1.150	0.053	0.045
E1	2.400	1.800	0.094	0.071
e	0.65BSC		0.026BSC	
L1	0.350	0.100	0.014	0.004